

Plastic-Encapsulate Diodes

Schottky Barrier Diode

FEATURES

- ⌘ Small Surface Mounting Type
- ⌘ Low V_F and I_R
- ⌘ High Reliability

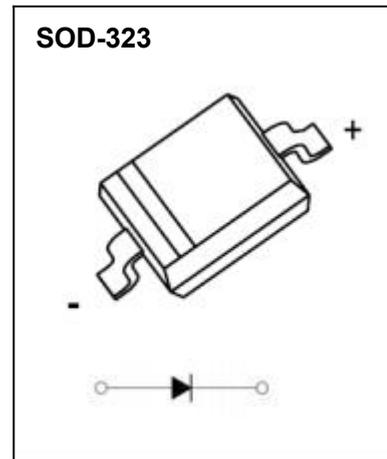
APPLICATIONS

- ⌘ General Rectification

MARKING: SS



The marking bar indicates the cathode

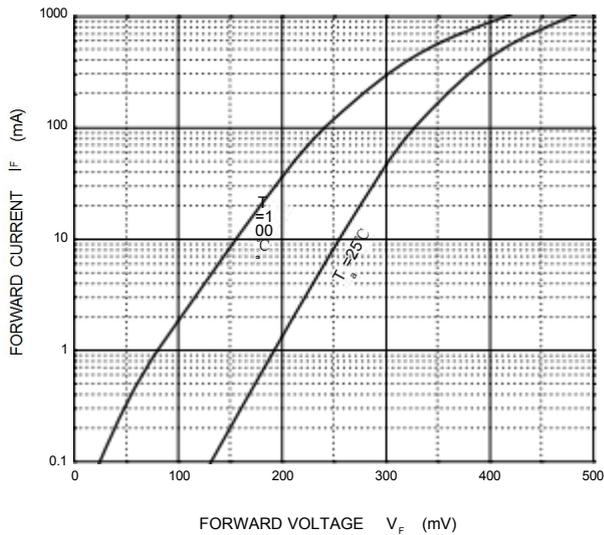
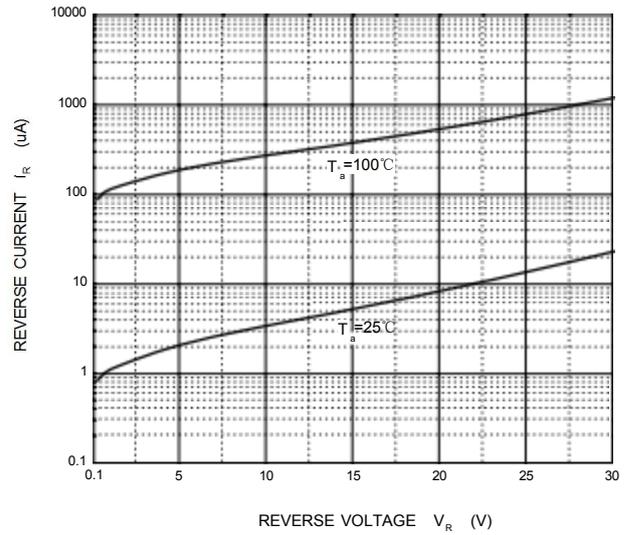
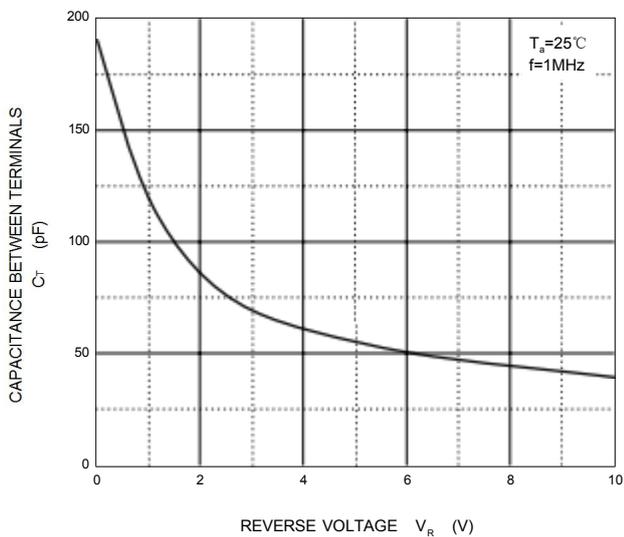


MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RM}	Non-Repetitive Peak Reverse Voltage	30	V
I_o	Continuous Forward Current	1	A
I_{FSM}	Non-repetitive Peak Forward Surge Current@ $t=8.3\text{ms}$	3	A
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	500	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	125	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=1\text{mA}$	30			V
Reverse current	I_R	$V_R=10\text{V}$			0.03	mA
Forward voltage	V_F	$I_F=700\text{mA}$			0.49	V
		$I_F=1\text{A}$			0.56	

Typical Characteristics
Forward Characteristics

Reverse Characteristics

Capacitance Characteristics

Power Derating Curve
